| Form 1449 (Modified) | Atty Docket No. | Application No.: |
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| | **UNTYP027** | **10/665,882** |
| **Information Disclosure Statement By Applicant** | Applicant: **RINERSON et al.** | |
| | Filing Date | Group |
| (Use Several Sheets if Necessary) | **September 19, 2003** | **2811** |

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**Foreign Patent or Published Foreign Patent Application**

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